Silicon NPN Epitaxial

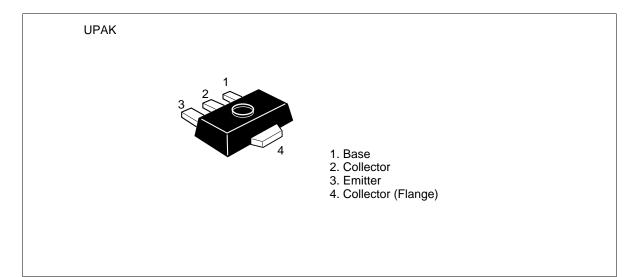
HITACHI

ADE-208-1145 (Z) 1st. Edition Mar. 2001

Application

Low frequency power amplifier

Outline





Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	25	V
Collector to emitter voltage	V _{CEO}	20	V
Emitter to base voltage	V _{EBO}	5	V
Collector current	Ι _c	1	А
Collector peak current	i _{C(peak)} *1	1.5	А
Collector power dissipation	P _c * ²	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

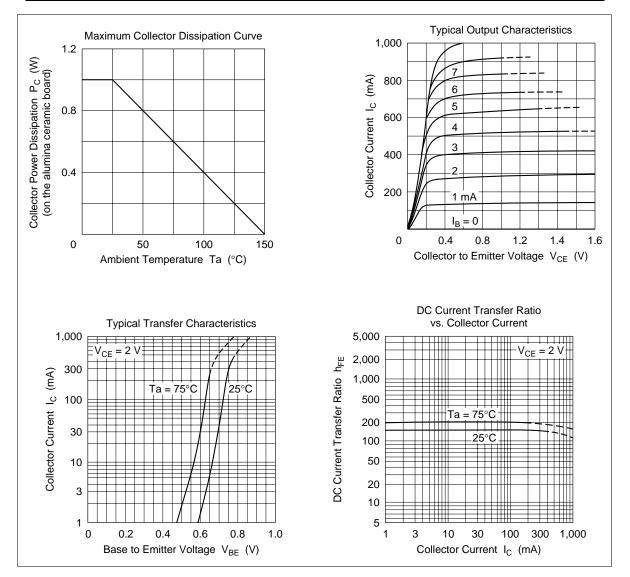
Notes: 1. $PW \le 10 \text{ ms}$, $Duty cycle \le 20\%$.

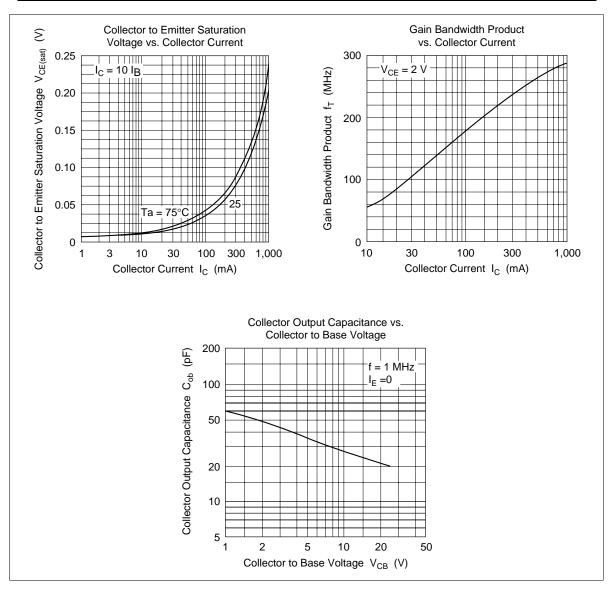
2. Value on the alumina ceramic board (12.5 \times 20 \times 0.7 mm)

Electrical Characteristics (Ta = 25°C)

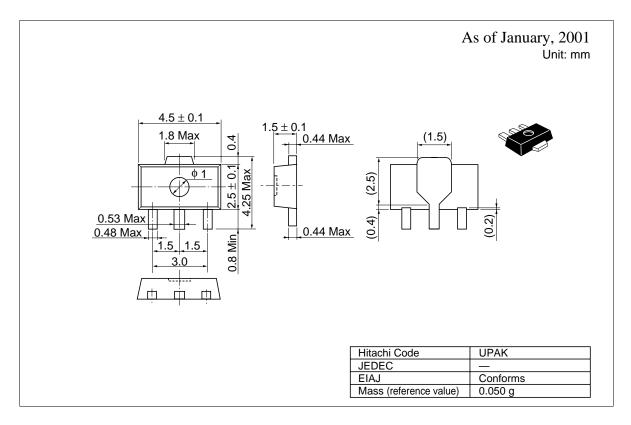
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\rm (BR)CBO}$	25	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{\rm (BR)CEO}$	20	_	_	V	$I_c = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	—	_	0.1	μΑ	$V_{CB} = 20 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	—		0.1	μΑ	$V_{EB} = 4 V, I_{C} = 0$
DC current transfer ratio	h_{FE}^{*1}	85	_	240		V_{ce} = 2 V, I_c = 0.5 A, Pulse
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	0.15	0.3	V	$I_{c} = 0.8 \text{ A}, I_{B} = 0.08 \text{ A}, \text{Pulse}$
Base to emitter saturation voltage	$V_{\text{BE(sat)}}$	_	0.9	1.0	V	$I_{c} = 0.8 \text{ A}, I_{B} = 0.08 \text{ A}, \text{Pulse}$
Gain bandwidth product	f _T	—	240	_	MHz	V_{ce} = 2 V, I_c = 0.5 A, Pulse
Collector output capacitance	Cob	_	22		pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$
Note: 1. The 2SD1366 is grouped by h _{FE} as follows.						
Mark AA Al	В					

h_{FE} 85 to 170 120 to 240





Package Dimensions



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